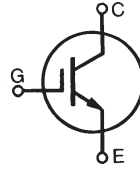


XPT™ 650V IGBT

GenX3™

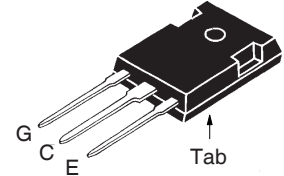
IXYH120N65B3

Extreme Light Punch Through
IGBT for 10-30kHz Switching



$$\begin{aligned} V_{CES} &= 650V \\ I_{C110} &= 120A \\ V_{CE(sat)} &\leq 1.90V \\ t_{fi(typ)} &= 107ns \end{aligned}$$

TO-247



G = Gate C = Collector
E = Emitter Tab = Collector

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C to } 175^\circ\text{C}$	650	V
V_{CGR}	$T_J = 25^\circ\text{C to } 175^\circ\text{C}, R_{GE} = 1M\Omega$	650	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$ (Chip Capability)	340	A
I_{LRMS}	Terminal Current Limit	160	A
I_{C110}	$T_C = 110^\circ\text{C}$	120	A
I_{CM}	$T_C = 25^\circ\text{C}, 1\text{ms}$	770	A
I_A	$T_C = 25^\circ\text{C}$	60	A
E_{AS}	$T_C = 25^\circ\text{C}$	1	J
SSOA (RBSOA)	$V_{GE} = 15V, T_{VJ} = 150^\circ\text{C}, R_G = 2\Omega$ Clamped Inductive Load	$I_{CM} = 240$ $V_{CE} \leq V_{CES}$	A
t_{sc} (SCSOA)	$V_{GE} = 15V, V_{CE} = 400V, T_J = 150^\circ\text{C}$ $R_G = 82\Omega, \text{Non Repetitive}$	8	μs
P_C	$T_C = 25^\circ\text{C}$	1360	W
T_J		-55 ... +175	$^\circ\text{C}$
T_{JM}		175	$^\circ\text{C}$
T_{stg}		-55 ... +175	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering	300	$^\circ\text{C}$
T_{SOLD}	1.6 mm (0.062in.) from Case for 10s	260	$^\circ\text{C}$
M_d	Mounting Torque	1.13/10	Nm/lb.in
Weight		6	g

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250\mu\text{A}, V_{GE} = 0V$	650		V
$V_{GE(th)}$	$I_C = 250\mu\text{A}, V_{CE} = V_{GE}$	3.5		6.0 V
I_{CES}	$V_{CE} = V_{CES}, V_{GE} = 0V$ $T_J = 150^\circ\text{C}$			25 μA 1 mA
I_{GES}	$V_{CE} = 0V, V_{GE} = \pm 20V$			± 100 nA
$V_{CE(sat)}$	$I_C = 100A, V_{GE} = 15V, \text{Note 1}$ $T_J = 150^\circ\text{C}$	1.55 1.77		V V

Features

- Optimized for 10-30kHz Switching
- Square RBSOA
- Avalanche Rated
- Short Circuit Capability
- High Current Handling Capability
- International Standard Package

Advantages

- High Power Density
- Low Gate Drive Requirement

Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts

Symbol Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)		Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$I_C = 60\text{A}, V_{CE} = 10\text{V}, \text{Note 1}$	35	58	S
C_{ies}	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		6900	pF
C_{oes}			393	pF
C_{res}			146	pF
$Q_{g(on)}$	$I_C = 120\text{A}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$		250	nC
Q_{ge}			52	nC
Q_{gc}			110	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = 50\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 400\text{V}, R_G = 2\Omega$ Note 2		30	ns
t_{ri}			28	ns
E_{on}			1.34	mJ
$t_{d(off)}$			168	ns
t_{fi}			107	ns
E_{off}			1.50	mJ
$t_{d(on)}$	Inductive load, $T_J = 150^\circ\text{C}$ $I_C = 50\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 400\text{V}, R_G = 2\Omega$ Note 2		30	ns
t_{ri}			30	ns
E_{on}			2.60	mJ
$t_{d(off)}$			226	ns
t_{fi}			196	ns
E_{off}			2.20	mJ
R_{thJC}				0.11 $^\circ\text{C/W}$
R_{thCS}		0.21		$^\circ\text{C/W}$

Notes:

1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.
2. Switching times & energy losses may increase for higher $V_{CE}(\text{clamp})$, T_J or R_G .

PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
by one or more of the following U.S. patents:	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

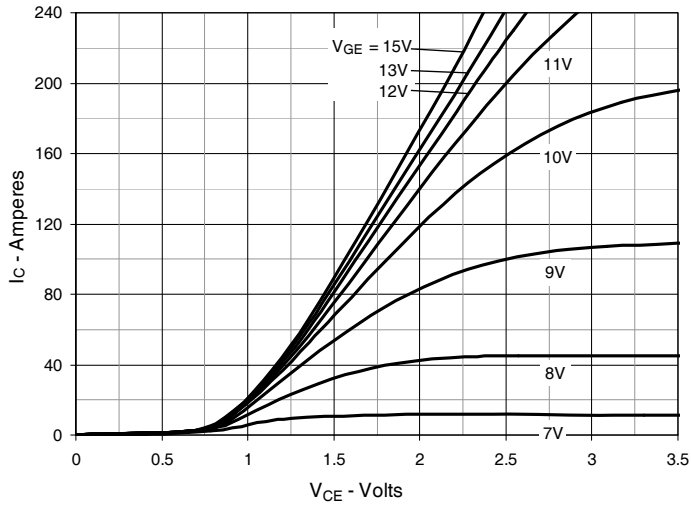
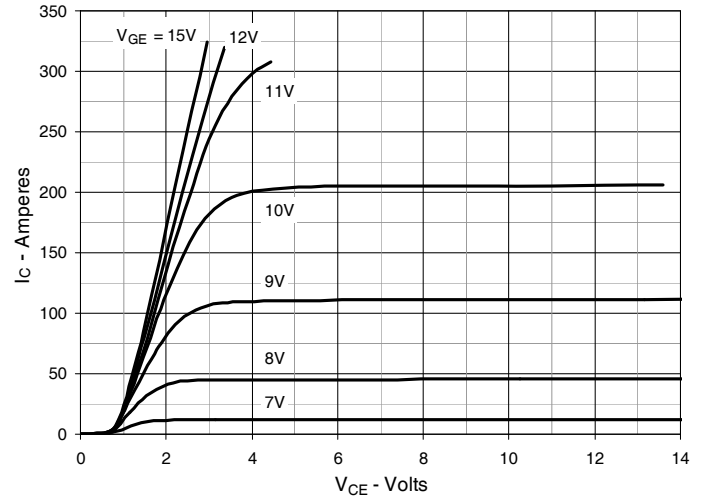
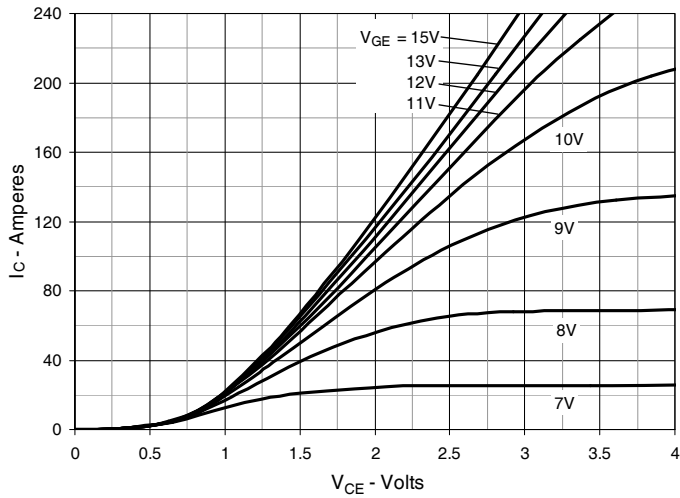
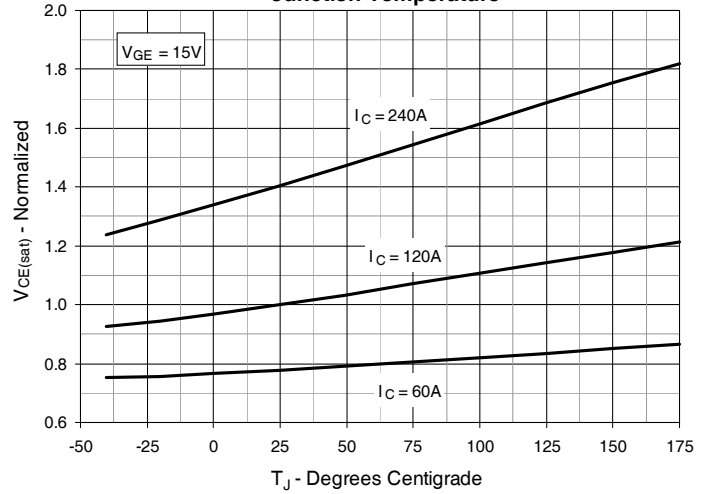
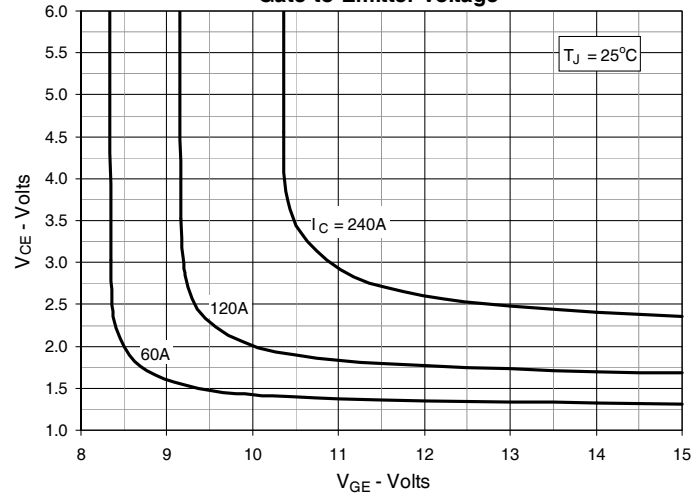
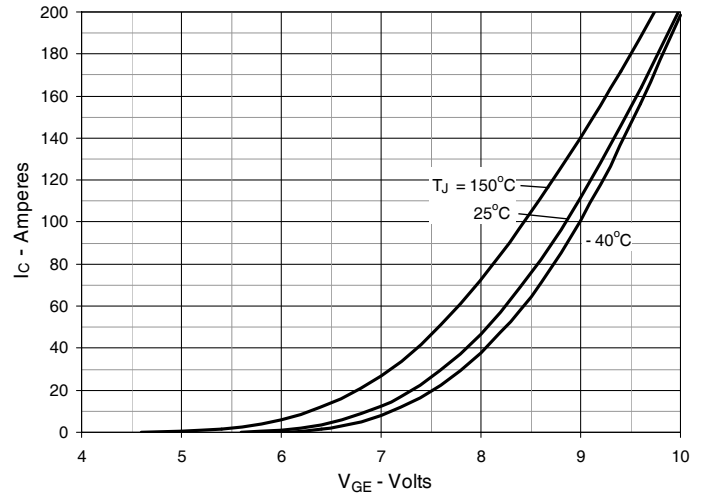
Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 3. Output Characteristics @ $T_J = 150^\circ\text{C}$

Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

Fig. 6. Input Admittance


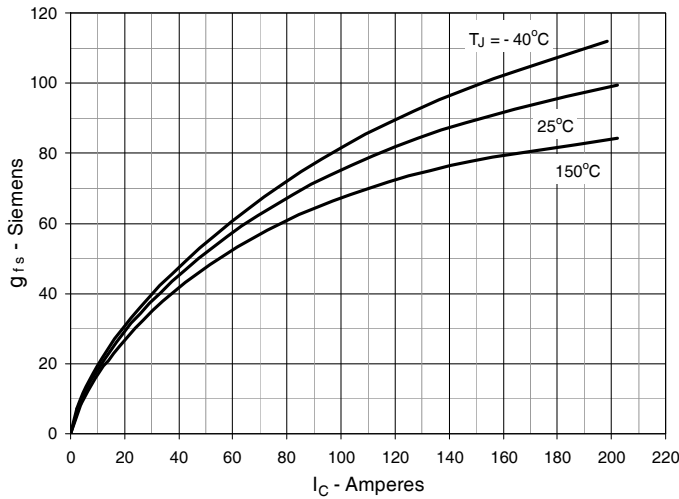
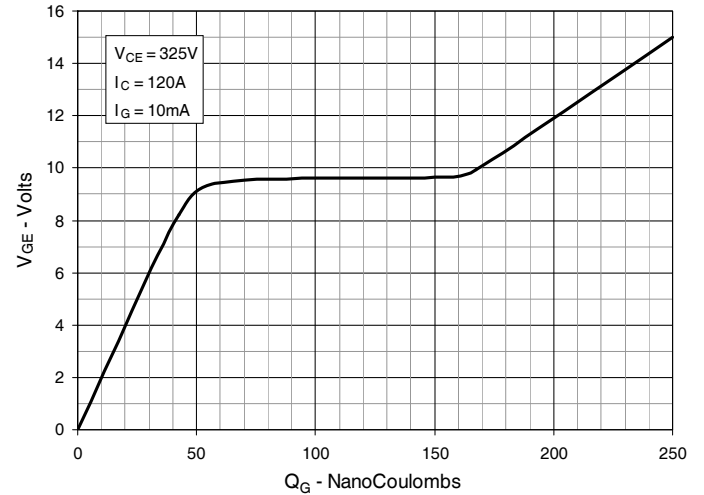
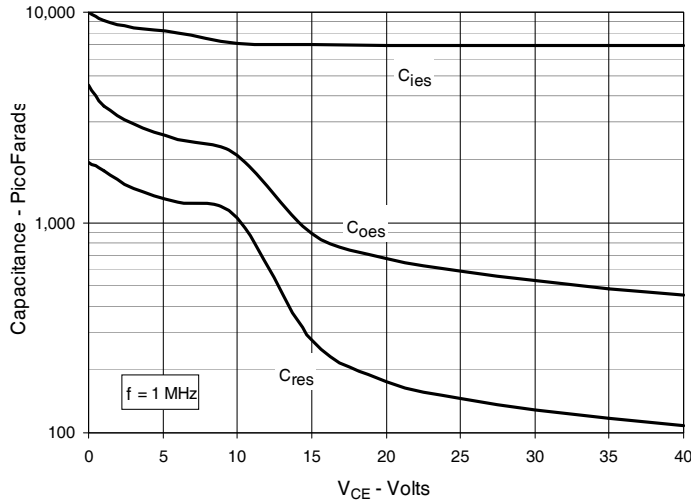
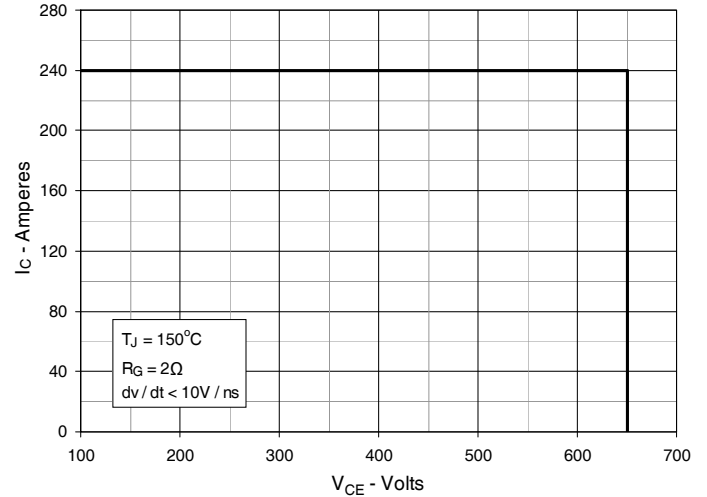
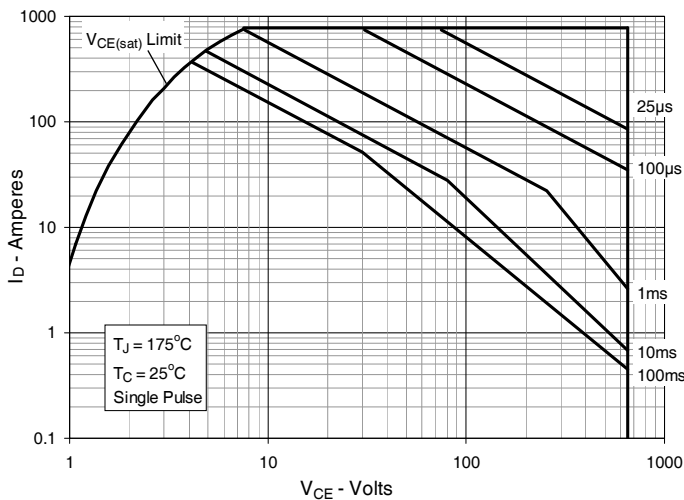
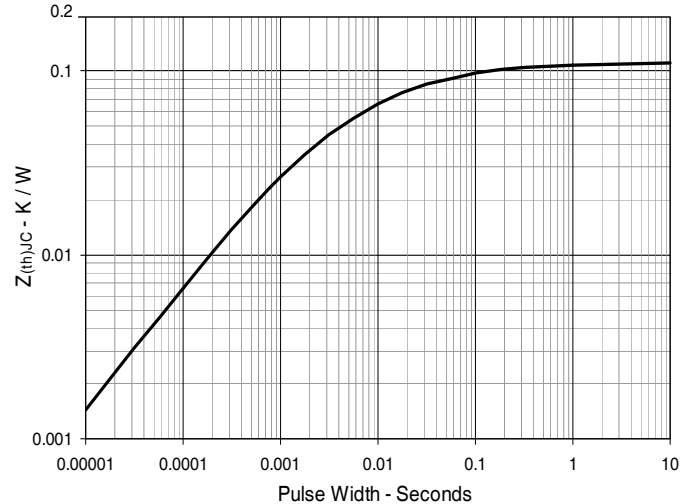
Fig. 7. Transconductance

Fig. 8. Gate Charge

Fig. 9. Capacitance

Fig. 10. Reverse-Bias Safe Operating Area

Fig. 11. Forward-Bias Safe Operating Area

Fig. 12. Maximum Transient Thermal Impedance


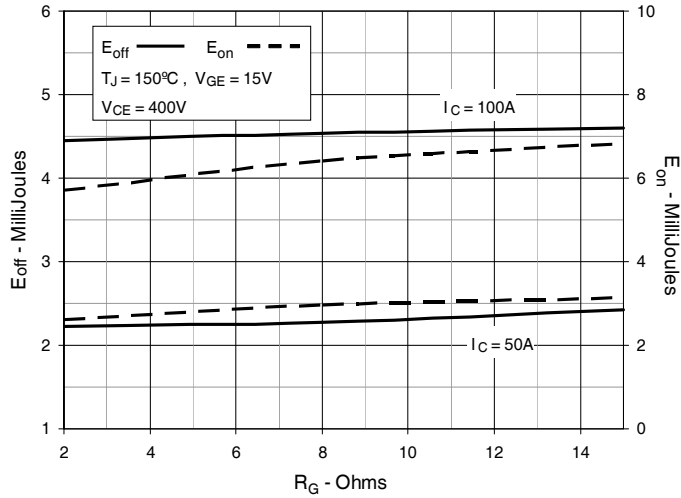
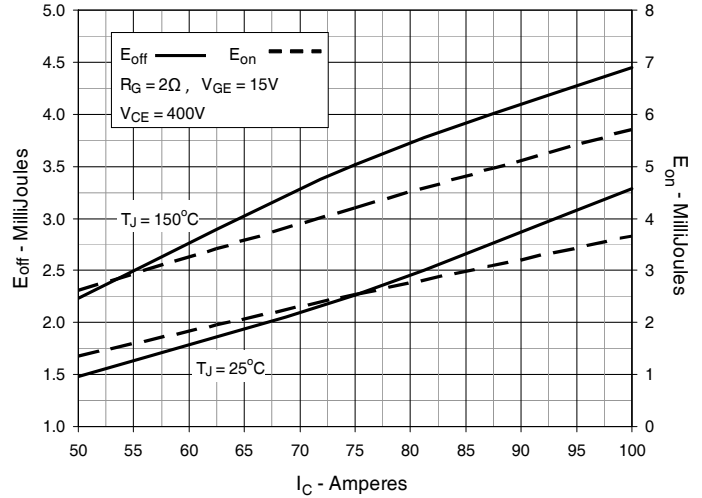
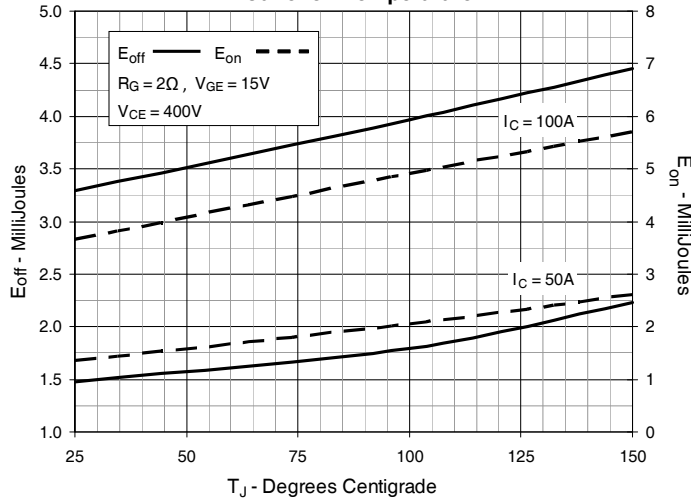
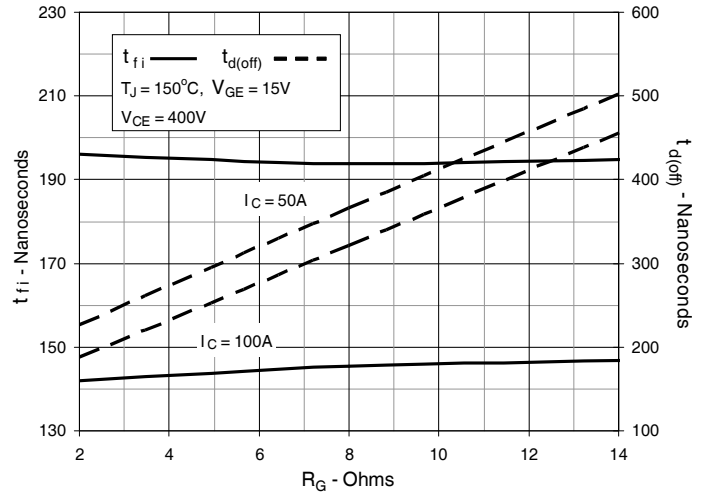
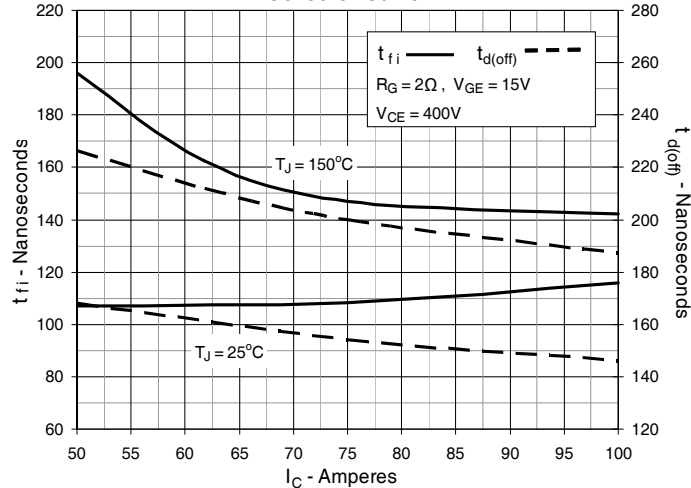
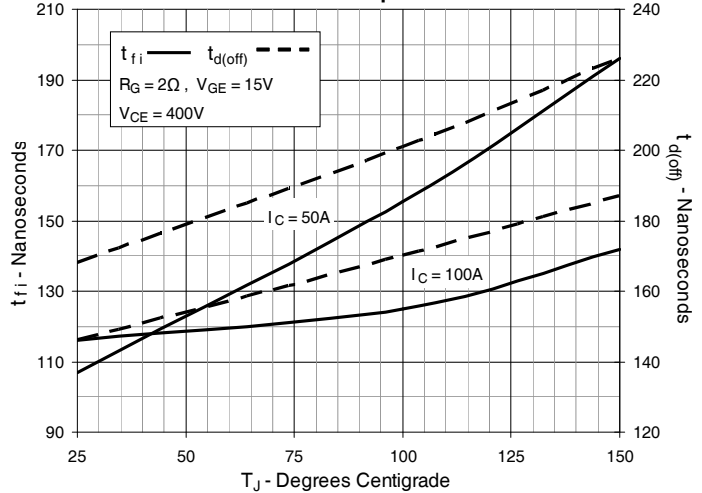
Fig. 13. Inductive Switching Energy Loss vs. Gate Resistance

Fig. 14. Inductive Switching Energy Loss vs. Collector Current

Fig. 15. Inductive Switching Energy Loss vs. Junction Temperature

Fig. 16. Inductive Turn-off Switching Times vs. Gate Resistance

Fig. 17. Inductive Turn-off Switching Times vs. Collector Current

Fig. 18. Inductive Turn-off Switching Times vs. Junction Temperature


Fig. 19. Inductive Turn-on Switching Times vs. Gate Resistance

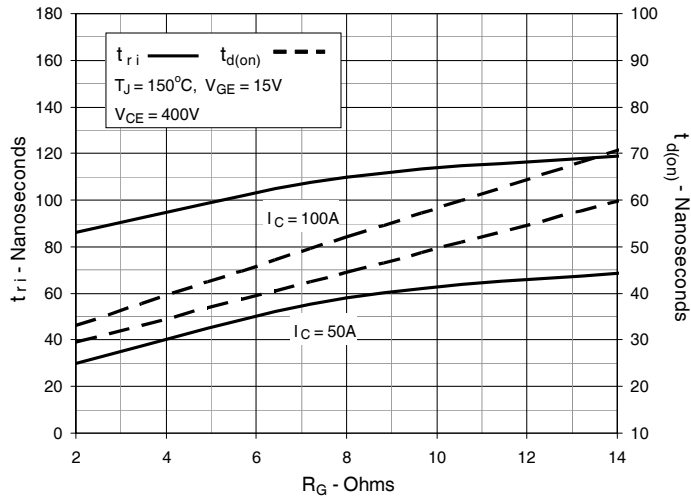


Fig. 20. Inductive Turn-on Switching Times vs. Collector Current

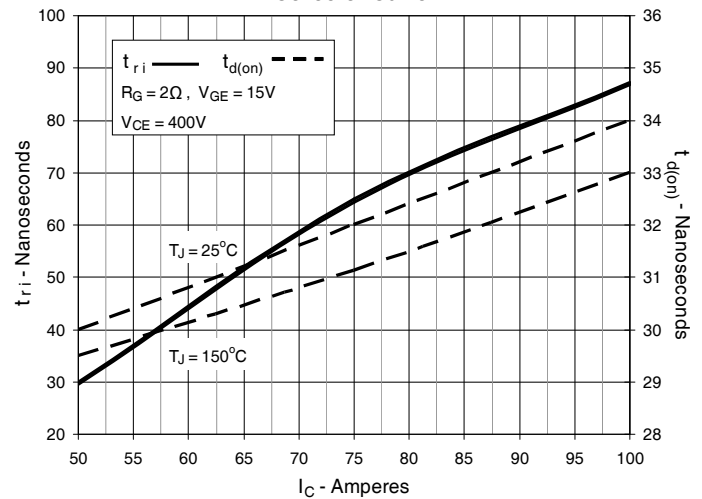
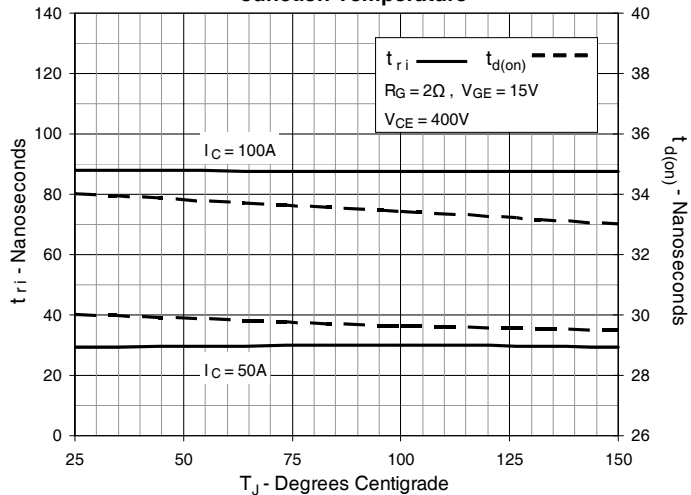
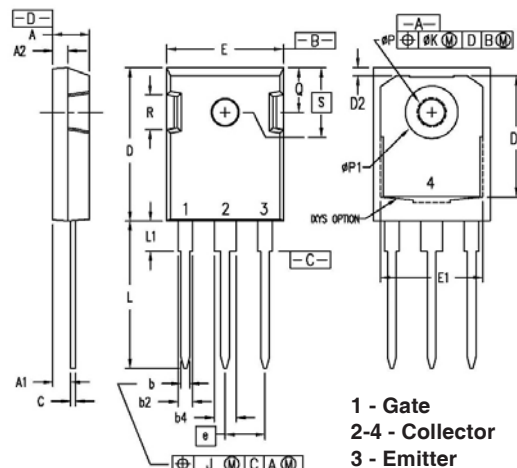


Fig. 21. Inductive Turn-on Switching Times vs. Junction Temperature



TO-247 OUTLINE



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.190	.205	4.83	5.21
A1	.090	.100	2.29	2.54
A2	.075	.085	1.91	2.16
b	.045	.055	1.14	1.40
b2	.075	.087	1.91	2.20
b4	.115	.126	2.92	3.20
C	.024	.031	0.61	0.80
D	.819	.840	20.80	21.34
D1	.650	.690	16.51	17.53
D2	.035	.050	0.89	1.27
E	.620	.635	15.75	16.13
E1	.545	.565	13.84	14.35
e	.215 BSC		5.45 BSC	
J	—	.010	—	0.25
K	—	.025	—	0.64
L	.780	.810	19.81	20.57
L1	.150	.170	3.81	4.32
ØP	.140	.144	3.55	3.65
ØP1	.275	.290	6.99	7.37
Q	.220	.244	5.59	6.20
R	.170	.190	4.32	4.83
S	.242 BSC		6.15 BSC	

NOTE: This drawing will meet all dimensions requirement of JEDEC outlines TO-247 AD (R-PSIP-F3)

